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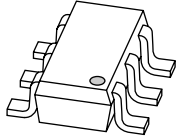
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Kind regards,

Team Nexperia



# PBSS4160DS

60 V, 1 A NPN/NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 04 — 11 December 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor pair in a SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

PNP/PNP complement: PBSS5160DS.

### 1.2 Features

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability:  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- Dual low power switches (e.g. motors, fans)
- Automotive applications

### 1.4 Quick reference data

Table 1. Quick reference data

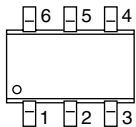
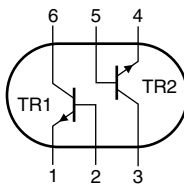
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$V_{CEO}$	collector-emitter voltage	open base	-	-	60	V
$I_C$	collector current		[1]	-	1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	2	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 1$ A; $I_B = 100$ mA	[2]	200	250	m $\Omega$

[1] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

[2] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

**Table 2. Pinning**

Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		

*sym020*

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS4160DS	SC-74	plastic surface mounted package (TSOP6); 6 leads	SOT457

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code
PBSS4160DS	B8

## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

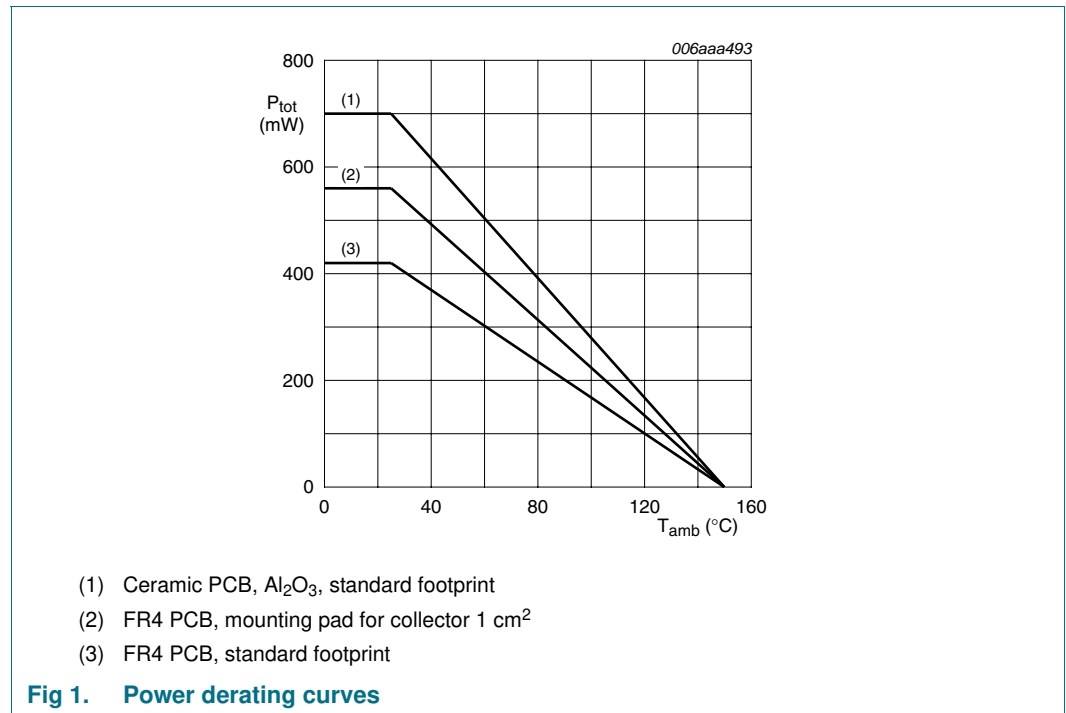
Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	-	80	V
$V_{CEO}$	collector-emitter voltage	open base	-	60	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
$I_C$	collector current	[1]	-	0.87	A
		[2]	-	1	A
		[3]	-	1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	2	A
$I_B$	base current		-	300	mA
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	1	A

**Table 5. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW
<b>Per device</b>						
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-65	+150	°C	
$T_{stg}$	storage temperature		-65	+150	°C	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

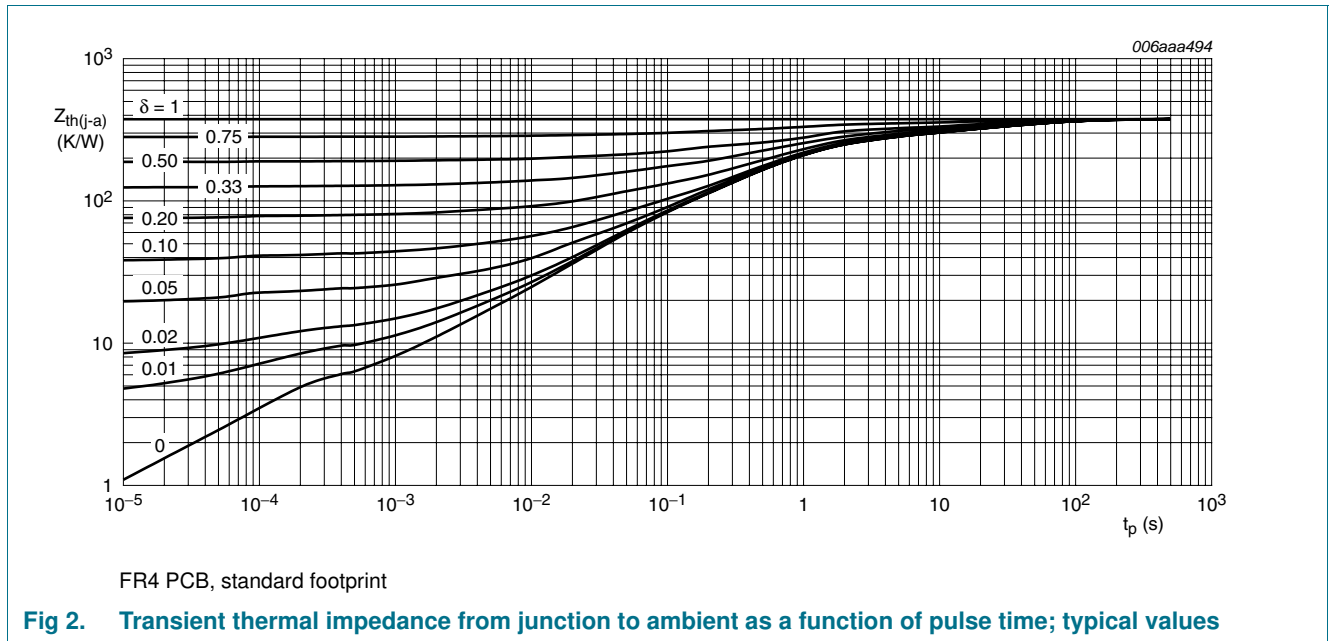


## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Per transistor</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	431	K/W
			[2]	-	-	338	K/W
			[3]	-	-	278	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W	
<b>Per device</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	298	K/W
			[2]	-	-	223	K/W
			[3]	-	-	179	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



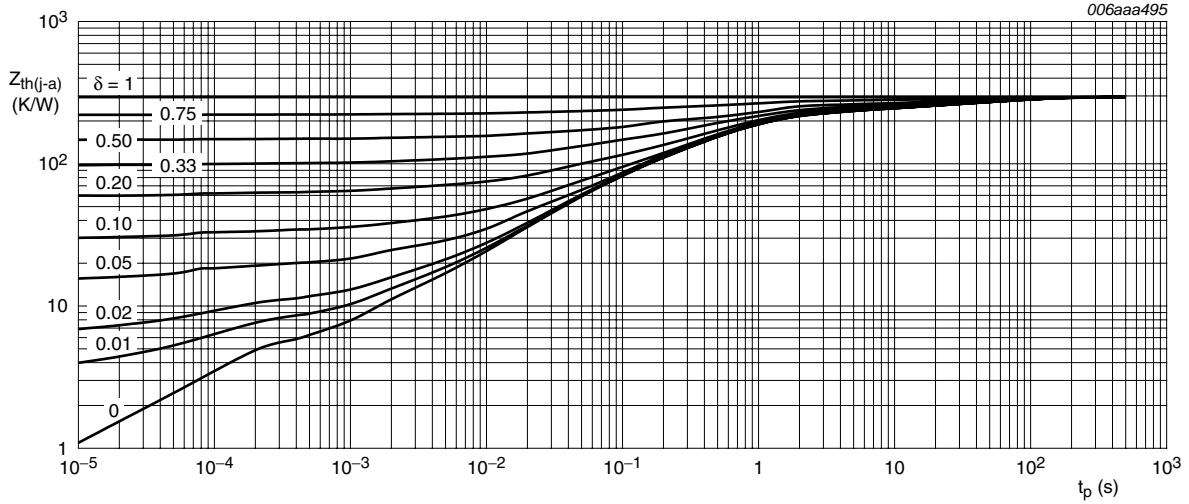


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

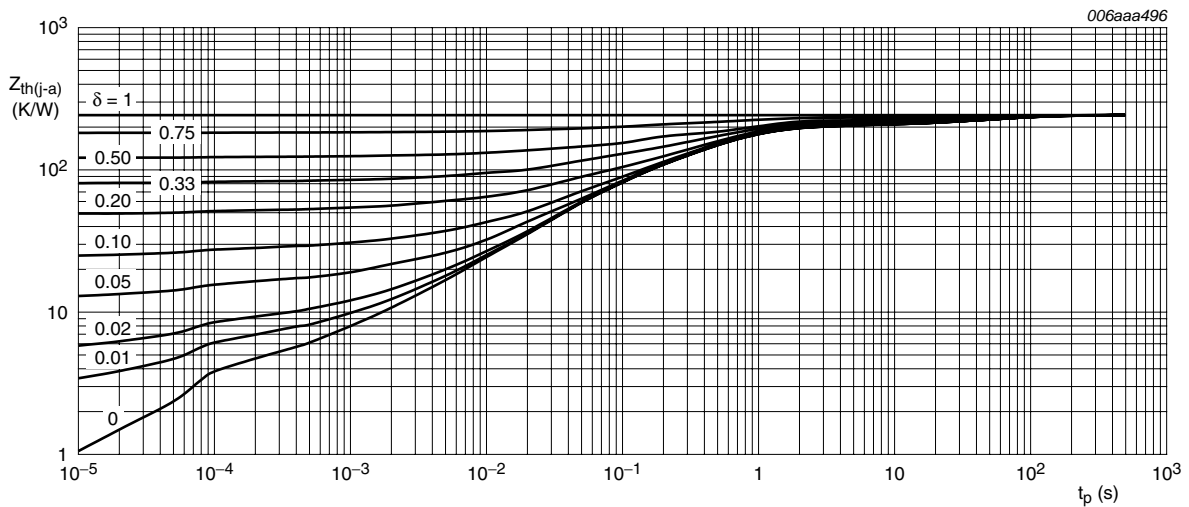


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

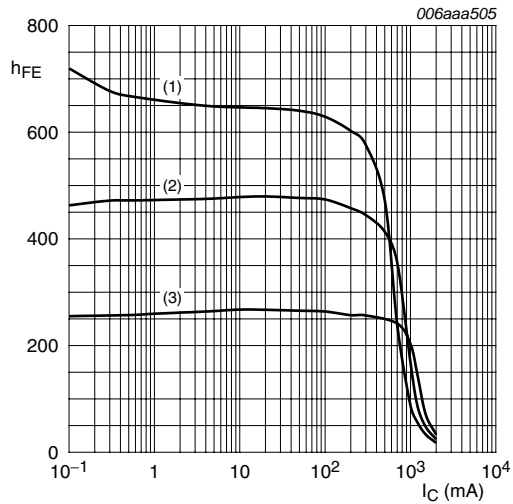
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

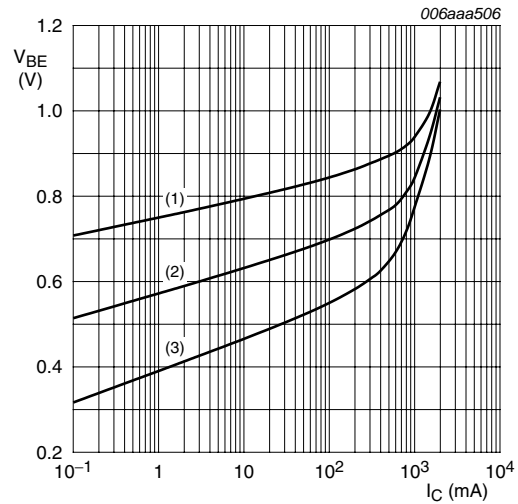
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = 60\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	250	500	-	
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	[1] 200	420	-	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	[1] 100	180	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	-	90	110	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	-	115	140	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	200	250	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	200	250	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}$	[1] -	0.95	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	[1] -	0.82	0.9	V
$t_d$	delay time	$I_C = 0.5\text{ A}; I_{Bon} = 25\text{ mA}; I_{Boff} = -25\text{ mA}$	-	11	-	ns
$t_r$	rise time		-	78	-	ns
$t_{on}$	turn-on time		-	90	-	ns
$t_s$	storage time		-	340	-	ns
$t_f$	fall time		-	160	-	ns
$t_{off}$	turn-off time		-	500	-	ns
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	150	220	-	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	5.5	10	pF

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



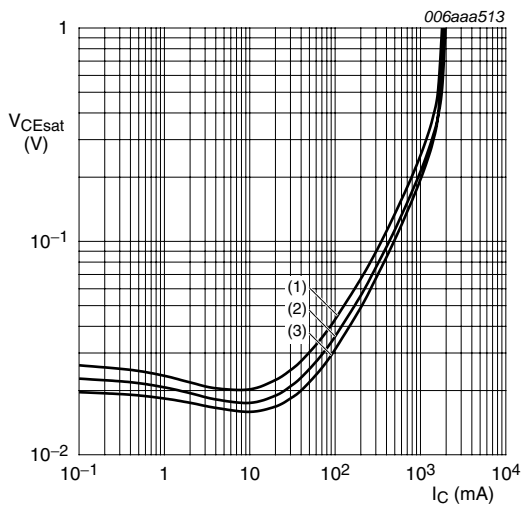
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig 5. DC current gain as a function of collector current; typical values**



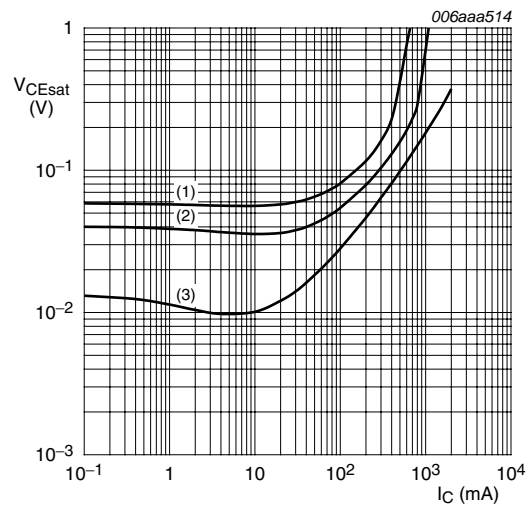
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig 6. Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

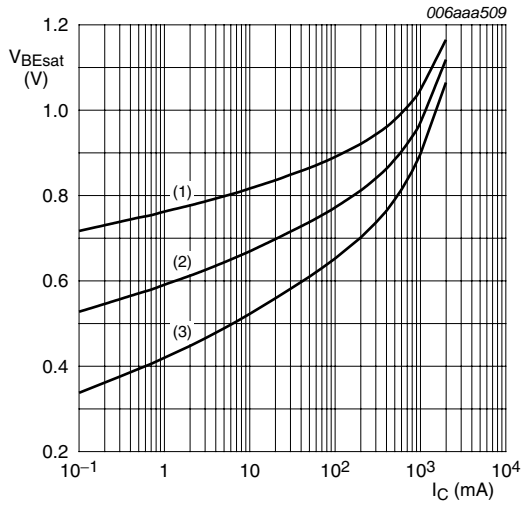
**Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values**



$T_{amb} = 25\text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

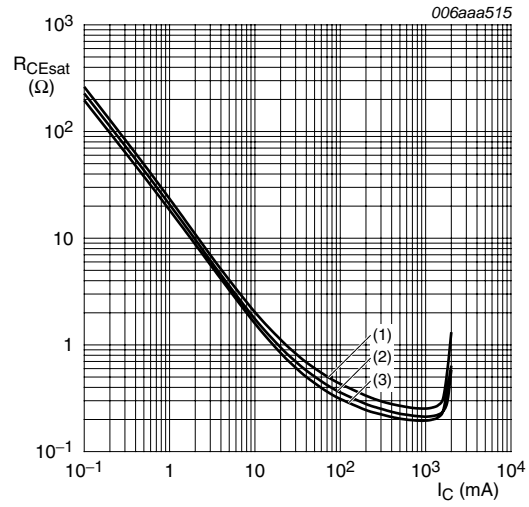
**Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values**





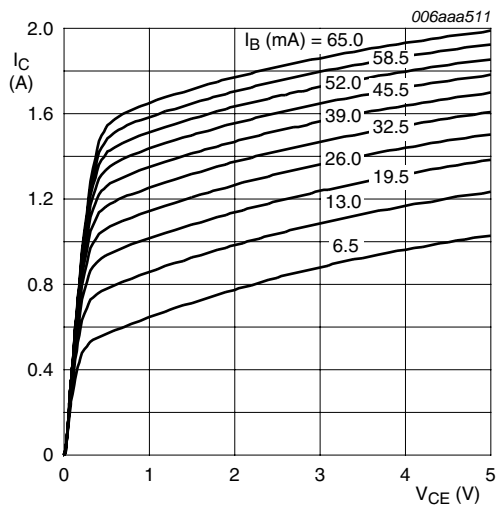
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55^\circ C$   
 (2)  $T_{amb} = 25^\circ C$   
 (3)  $T_{amb} = 100^\circ C$

**Fig 9. Base-emitter saturation voltage as a function of collector current; typical values**



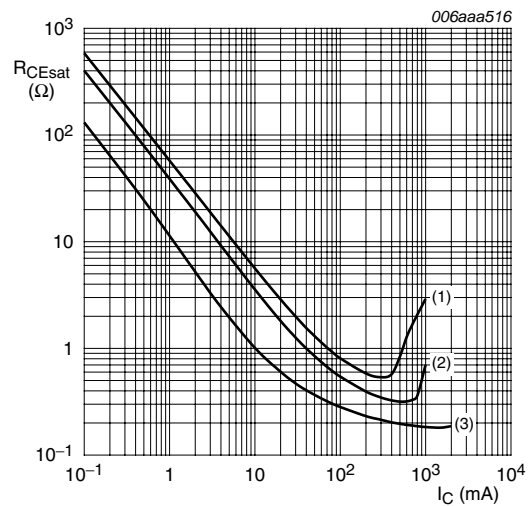
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100^\circ C$   
 (2)  $T_{amb} = 25^\circ C$   
 (3)  $T_{amb} = -55^\circ C$

**Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25^\circ C$

**Fig 11. Collector current as a function of collector-emitter voltage; typical values**



$T_{amb} = 25^\circ C$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**

8. Test information

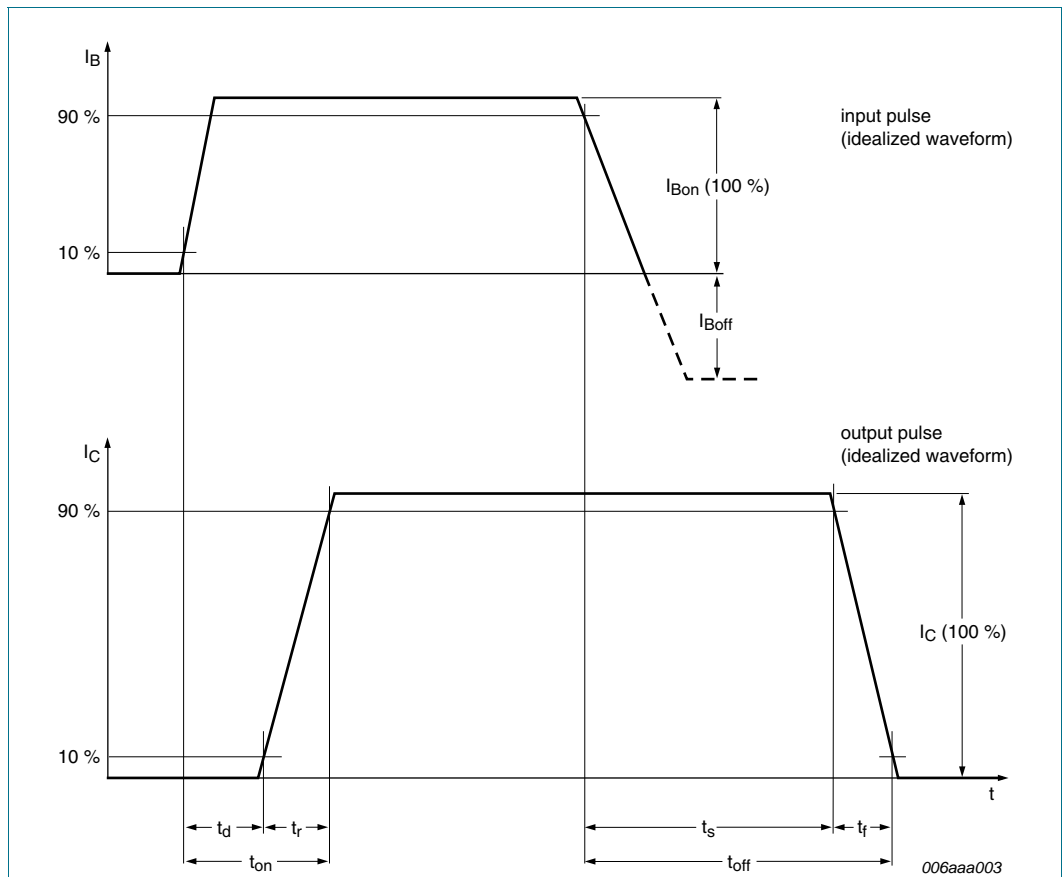
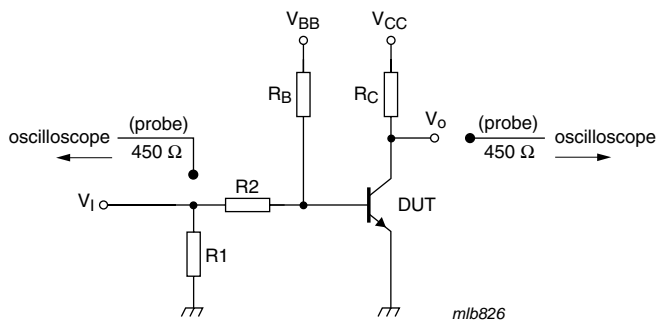


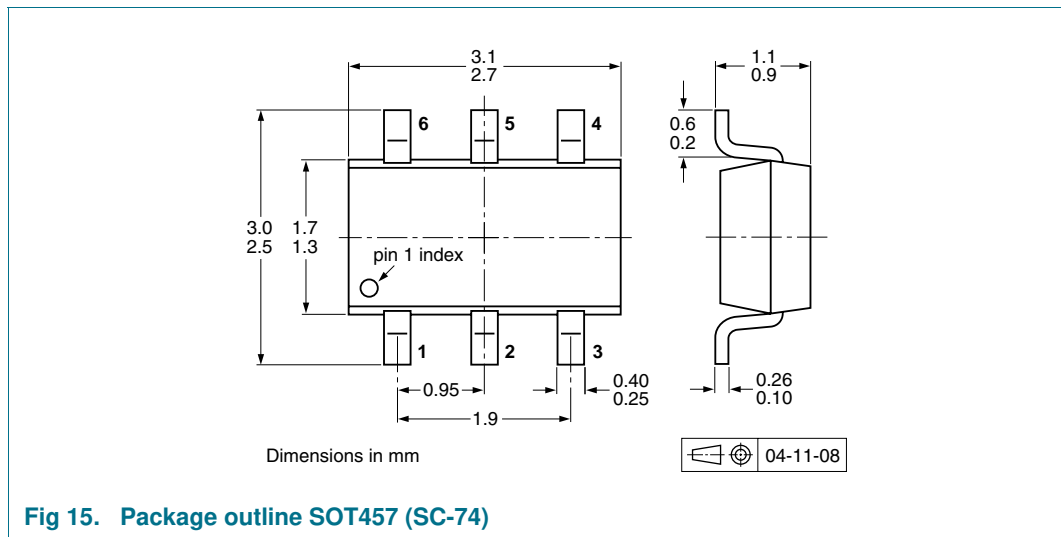
Fig 13. BISS transistor switching time definition



$I_C = 0.5 \text{ A}$ ;  $I_{B_{on}} = 25 \text{ mA}$ ;  $I_{B_{off}} = -25 \text{ mA}$ ;  $R_1 = \text{open}$ ;  $R_2 = 100 \text{ } \Omega$ ;  $R_B = 300 \text{ } \Omega$ ;  $R_C = 20 \text{ } \Omega$

Fig 14. Test circuit for switching times

## 9. Package outline



## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

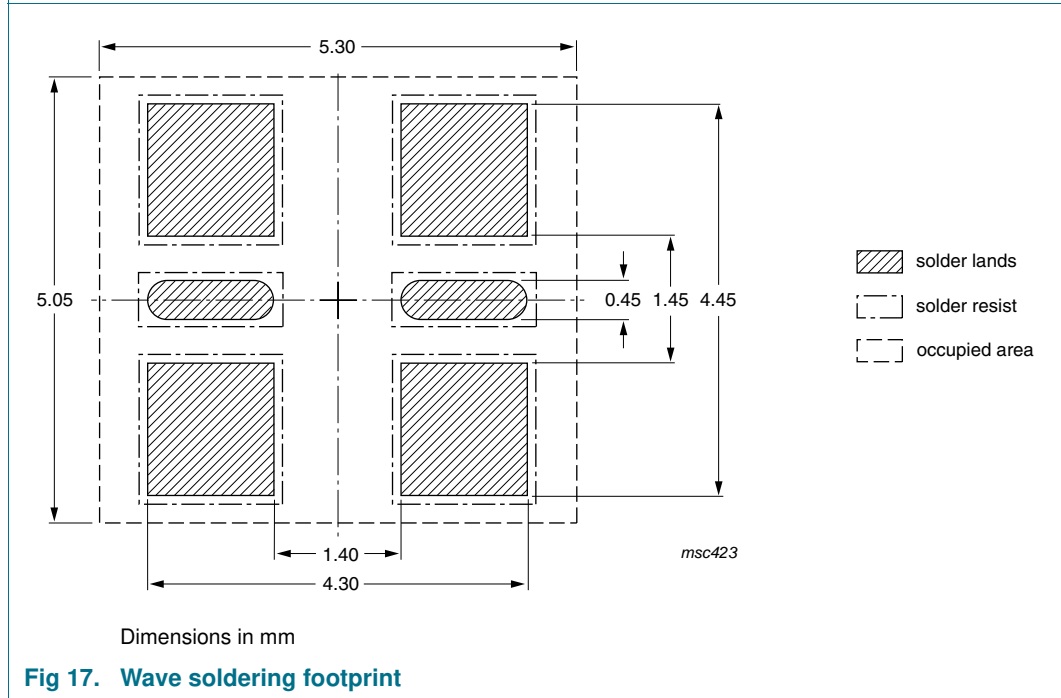
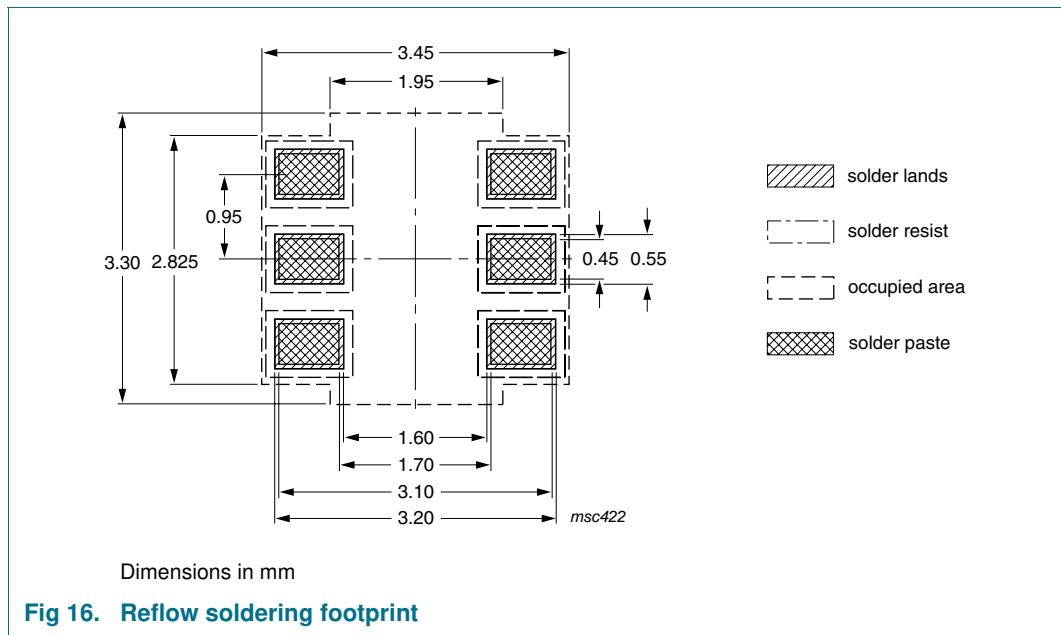
Type number	Package	Description	Packing quantity	
			3000	10000
PBSS4160DS	SOT457	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

**11. Soldering**



## 12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160DS_4	20091211	Product data sheet	-	PBSS4160DS_3
Modifications:		<ul style="list-style-type: none"><li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li><li><a href="#">Figure 17 "Wave soldering footprint"</a>: updated</li></ul>		
PBSS4160DS_3	20060209	Product data sheet	-	PBSS4160DS_2
PBSS4160DS_2	20050627	Product data sheet	-	PBSS4160DS_1
PBSS4160DS_1	20040426	Objective data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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